2SK1809

Silicon N-Channel MOS FET

HITACHI

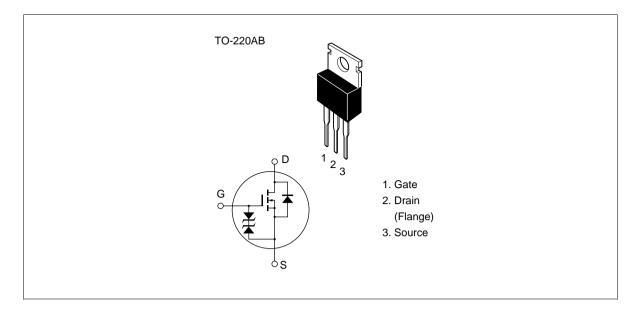
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switchingregulator, DC-DC converter

Outline





2SK1809

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{\scriptscriptstyle DSS}$	600	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	5	A
Drain peak current	I _{D(pulse)} *1	20	A
Body to drain diode reverse drain current	I _{DR}	5	A
Channel dissipation	Pch*2	60	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. PW \leq 10 μ s, duty cycle \leq 1 %

^{2.} Value at Tc = 25 °C

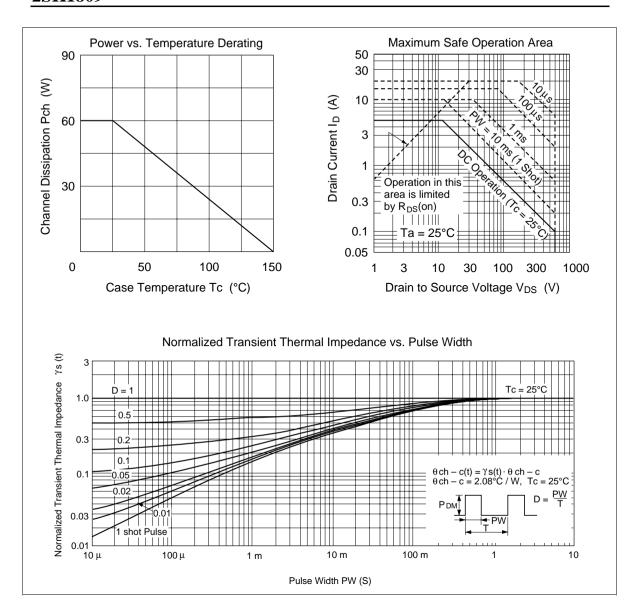
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	250	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{\rm GS(off)}$	2.0	_	3.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	_	1.1	1.5	Ω	$I_D = 2.5A$ $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	y _{fs}	3.0	5.0	_	S	$I_D = 2.5 \text{ A}$ $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	_	1000	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	250	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	45	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	12	_	ns	I _D = 2.5 A
Rise time	t _r	_	45	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	105	_	ns	$R_L = 12 \Omega$
Fall time	t _f	_	55	_	ns	
Body to drain diode forward voltage	V_{DF}	_	0.9	_	V	$I_F = 5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}		500		ns	$I_F = 5 \text{ A}, V_{GS} = 0,$ $di_F / dt = 100 \text{ A} / \mu \text{s}$

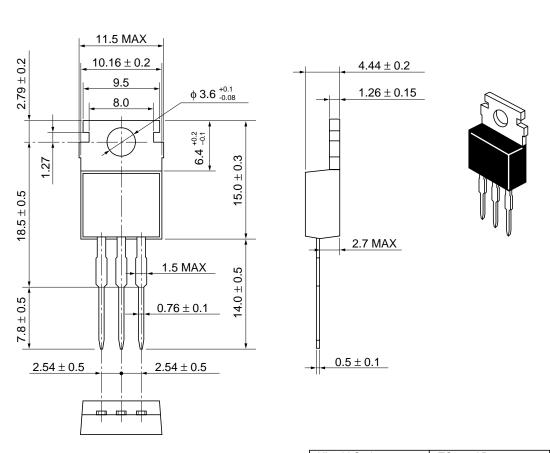
Note 1. Pulse Test

See characteristic curves of 2SK1404

2SK1809



Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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